

Form PTO-1449

Docket Number 577182000100

Application Number 10/810,070

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

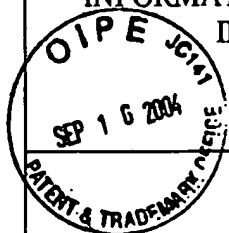
Applicant

Sudhanshu MISRA et al.

Filing Date March 25, 2004

Group Art Unit 3723

Mailing Date September 17, 2004



U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
R	1.	11/01/2001	2001/0036795	Merchant et al.			
	2.	11/01/2001	2001/0036796	Misra et al.			
	3.	12/26/2002	2002/197934	Paik			
	4.	03/20/2003	2003/0054735	Misra et al.			
	5.	02/04/1997	5,599,423	Parker et al.			
	6.	08/12/1997	5,655,951	Meikle et al.			
	7.	11/02/1999	5,975,991	Karlsrud			
	8.	02/29/2000	6,030,488	Izumi et al.			
	9.	06/20/2000	6,077,153	Fujita et al.			
	10.	07/18/2000	6,089,966	Arai et al.			
	11.	04/10/2001	6,214,732	Easter et al.			
	12.	07/10/2001	6,258,231	Easter et al.			
	13.	11/20/2001	6,319,095	Merchant et al.			
	14.	12/11/2001	6,328,633	Misra et al.			
	15.	04/02/2002	6,364,742	Fukuzawa			
	16.	04/02/2002	6,364,744	Merchant et al.			
	17.	04/09/2002	6,368,200	Merchant et al.			
	18.	04/23/2002	6,375,541	Merchant et al.			
	19.	08/20/2002	6,436,830	Merchant et al.			
	20.	08/27/2002	6,439,972	Misra et al.			
	21.	10/01/2002	6,458,016	Merchant et al.			
	22.	10/01/2002	6,458,289	Merchant et al.			
	23.	10/08/2002	6,461,225	Misra et al.			
	24.	07/29/2003	6,599,837	Merchant et al.			
	25.	12/09/2003	6,659,846	Misra et al.			
	26.	01/13/2004	6,676,483	Roberts			

EXAMINER:

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FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO	
W	27.	06/03/1998	EP 0 845 328	Europe	1	1		
	28.	06/02/1999	EP 0 919 336	Europe	1	1		
W	29.	12/27/2002	WO 02/102549	WIPO	1	1		

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)


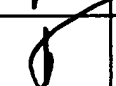
Examiner Initials	Ref. No.	Title
W	30.	Boning, D. et al. (April 1999). "Pattern Dependent Modeling for CMP Optimization and Control," <i>Proc. Symposium P: Chemical Mechanical Polishing</i> , pp. 1-13.
	31.	Chen, Y. et al. (June 2000). "Practical Iterated Fill Synthesis for CMP Uniformity," prepared by the Computer Science Departments of UCLA, the University of Virginia, and Georgia State University, 4 pages.
	32.	Fu, G. et al. (2002). "A Model for Wafer Scale Variation of Material Removal Rate in Chemical Mechanical Polishing Based on Viscoelastic Pad Deformation," <i>Journal of Electronic Materials</i> 31(10):1066-1073.
	33.	Gostein, M. et al. (March 2002). "Characterizing and Monitoring Copper CMP Using Nondestructive Optoacoustic Metrology," provided by Micromagazine.com, located at http://www.micromagazine.com/archive/02/03/gostein.html , last visited on March 4, 2004, 13 pages.
	34.	Luo, J. et al. (May 2001). "Material Removal Mechanism in Chemical Mechanical Polishing: Theory and Modeling," <i>IEEE Transactions on Semiconductor Manufacturing</i> 14(2):112-133.
	35.	Noh, K. et al. (January 2002). "Mechanics, Mechanisms and Modeling of the Chemical Mechanical Polishing Process," 10 pages.
	36.	Oji, C. et al. (2000). "Wafer Scale Variation of Planarization Length in Chemical Mechanical Polishing," <i>Journal of the Electrochemical Society</i> 147(11):4307-4312.
	37.	Ouma, D. O. et al. (May 2002). "Characterization and Modeling of Oxide Chemical Mechanical Polishing Using Planarization Length and Pattern Density Concepts," <i>IEEE Transactions on Semiconductor Manufacturing</i> 15(2):232-244.
W	38.	Philipossian, A. et al. (2003). "Fundamental Tribological and Removal Rate Studies of Inter-Layer Dielectric Chemical Mechanical Planarization," <i>Japan J. Appl. Phys</i> 42(10):6371-6379.
	39.	SKW Associates, Inc. (Date Unknown). "Planarization Length: Concept and Determination in Dielectric CMP Process," 2 pages.

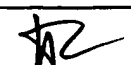
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	40.	Stine, B. et al. (Feb 1998). "Rapid Characterization and Modeling of Pattern Dependent Variation in Chemical Polishing," <i>IEEE Transactions on Semiconductor Manufacturing</i> 11(1):129-140.
	41.	Tung, T-L (September 1997). "A Method for Die-Scale Simulation of CMP Planarization," <i>IEEE</i> pp. 65-68.

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